

ABSTRACT

ANTIREFLECTIVE COATING FOR USE DURING THE MANUFACTURE OF A SEMICONDUCTOR DEVICE

An antireflective layer formed from boron-doped amorphous carbon can be removed using a process which is less likely to over etch a dielectric layer than conventional technology. This layer can be removed by exposing the layer to an oxygen plasma (i.e. an "ashing" process), preferably concurrently with the ashing and removal of an overlying photoresist layer. An inventive process which uses the inventive antireflective layer is also described.